
2SC1907

Silicon NPN Epitaxial Planar

HITACHI

Application

UHF TV Tuner, Local oscillator

Outline

TO-92 (2)



- 1. Emitter
- 2. Collector
- 3. Base

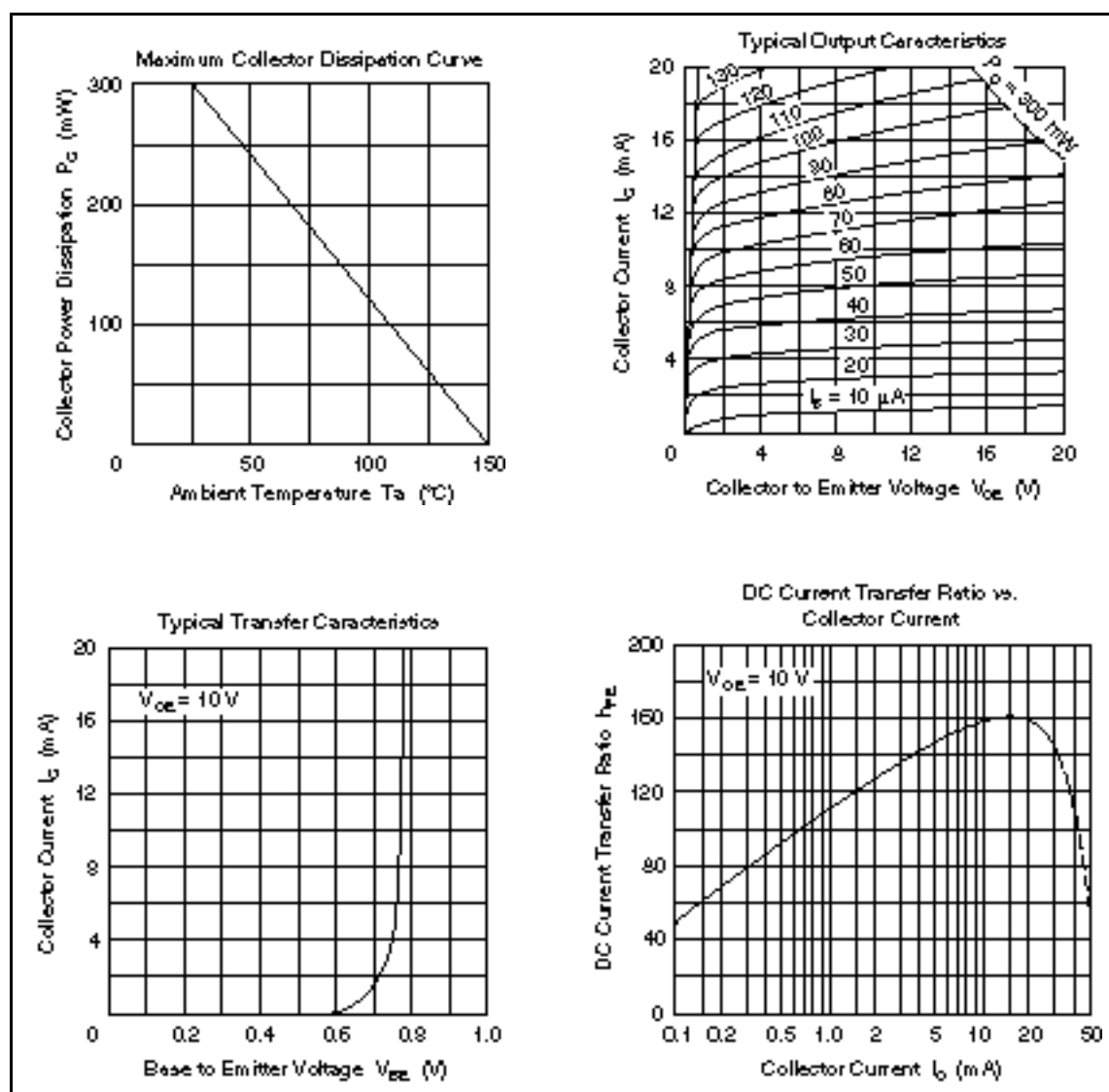
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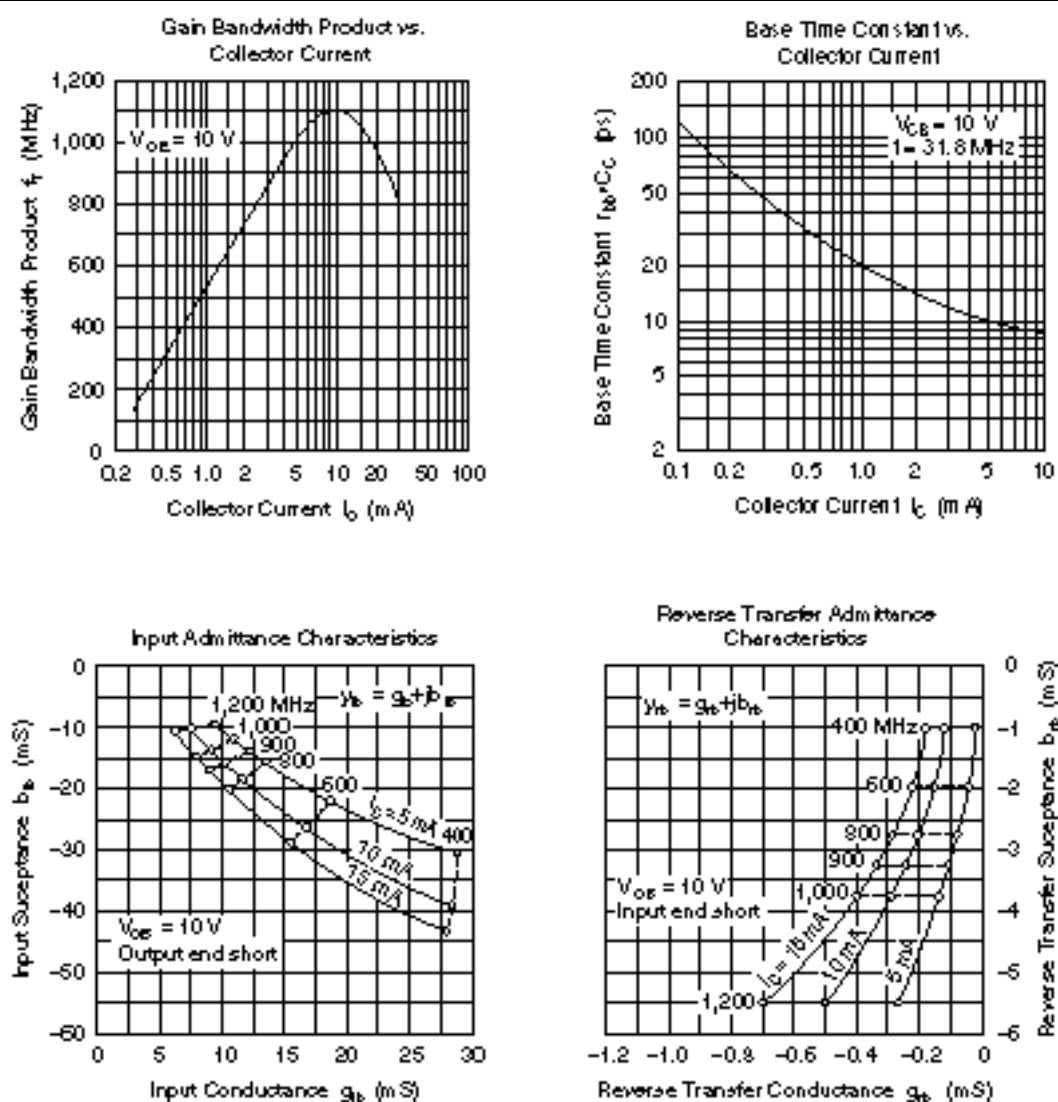
Absolute Maximum Ratings (Ta = 25°C)

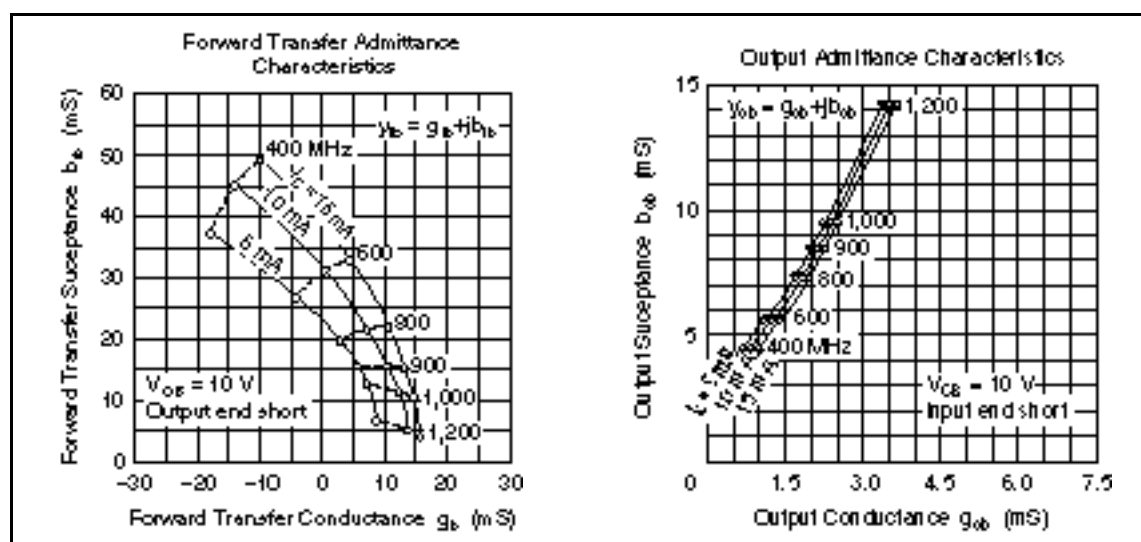
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	19	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	50	mA
Emitter current	I_E	−50	mA
Collector power dissipation	P_C	300	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	19	—	—	V	$I_C = 3 \text{ mA}, R_{BE} = \bullet$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	2	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 10 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE}	40	—	—		$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.2	1.0	V	$I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$
Collector output capacitance	C_{ob}	—	1.0	2.0	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f_T	900	1100	—	MHz	$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$
Base time constant	$r_{bb'} \cdot C_C$	—	10	25	ps	$V_{CB} = 10 \text{ V}, I_C = 10 \text{ mA}, f = 31.8 \text{ MHz}$
Oscillation output power	P_{out}	—	8	—	mW	$V_{CB} = 10 \text{ V}, I_C = 10 \text{ mA}, f = 930 \text{ MHz}$







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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brea, CA 94005-4835

U.S.A.

Tel 415-589-8300

Fax 415-583-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Danrecker Straße 3

D-85622 Feldkirchen

München

Tel 089-9 94 80-0

Fax 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

High Wycombe

Berkshire SL6 8YA

United Kingdom

Tel 0628-885000

Fax 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0404

Tel 535-2100

Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074